

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions and listings of claims in the application:

1-18. (Canceled)

19. (New) A method for processing a substrate, comprising:  
delivering said substrate to be plasma-processed into a process chamber;  
introducing a process gas into said process chamber while an inside of said process chamber is evacuated by a first exhaust port in said process chamber;  
plasma-processing said substrate; and  
introducing, after said substrate is plasma-processed, a cleaning gas into said process chamber while the inside of said process chamber is evacuated by a second exhaust port positioned lower than said first exhaust port in said process chamber, thereby cleaning the inside of said process chamber.

20. (New) The method as set forth in claim 19, wherein said first exhaust port is positioned higher than a surface of said substrate, and  
wherein said second exhaust port is positioned lower than the surface of said substrate.

21. (New) The method as set forth in claim 20, wherein said substrate is moved upward when said substrate is plasma-processed so that said first exhaust port is positioned higher than the surface of said substrate, and moved downward when the inside of said process chamber is cleaned so that the second exhaust is positioned lower than the surface of said substrate.

22. (New) The method as set forth in claim 19, wherein the inside of said process chamber is exhausted by the first and the second exhaust ports when said cleaning gas is introduced into said process chamber.

23. (New) The method as set forth in claim 19, wherein said cleaning gas is a reactive gas.

24. (New) The method as set forth in claim 23, further comprising:  
supplying a microwave into said process chamber when the inside of said process chamber is cleaned.

25. (New) The method as set forth in claim 20, wherein the inside of said process chamber is exhausted by the first and the second exhaust ports when said cleaning gas is introduced into said process chamber.

26. (New) The method as set forth in claim 20, wherein said cleaning gas is a reactive gas.

27. (New) The method as set forth in claim 26, further comprising:  
supplying a microwave into said process chamber when the inside of said  
process chamber is cleaned.
28. (New) The method as set forth in claim 21, wherein the inside of said  
process chamber is exhausted by the first and the second exhaust ports when said  
cleaning gas is introduced into said process chamber.
29. (New) The method as set forth in claim 21, wherein said cleaning gas is a  
reactive gas.
30. (New) The method as set forth in claim 29, further comprising:  
supplying a microwave into said process chamber when the inside of said  
process chamber is cleaned.